

### Features

- Can be used without external DC bias
- Exhibits uniform R<sub>v</sub> characteristics
- High Voltage Sensitivity
- P Type Schottky Diode
- Available in chip form (ODS-1261)
- RoHS Compliant\* and 260°C Reflow Compatible

### Description and Applications

The MA4E931Z2-1261A Zero Bias Detector (ZBD) diode is suitable for use in microstrip or stripline detector circuits. These chips can be used in automatic assembly processes due to their 0.004" gold bond pads and sturdy construction. Designed for high volume, low cost, detector applications.

### Maximum Ratings

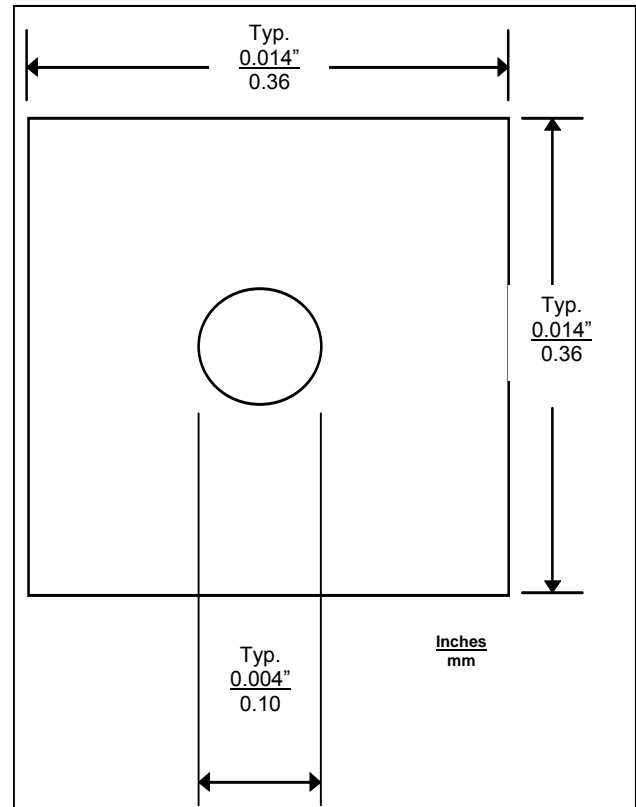
Parameter	Symbol	Unit	Values
Operating Temperature	T <sub>OP</sub>	°C	-65 to +150
Storage Temperature	T <sub>STG</sub>	°C	-65 to +150
Incident RF Power (CW)	P <sub>T</sub>	mW	75
Reverse Voltage @ 25 °C	V <sub>R</sub>	V	3

### Electrical Specifications @ +25 °C

Parameter	Condition	Symbo	Specificatio
Breakdown Voltage	I <sub>R</sub> = 1.0 mA	V <sub>B</sub>	3.0 V min.
Forward Voltage	I <sub>F</sub> = 1.0 mA	V <sub>F</sub>	150 mV typ.

### Chip Outline

#### MA4E931Z2-1261A



### RF Performance @ 10.0 GHz @ +25 °C

Parameter	Conditions	Typical
Tangential Signal Sensitivity	BW = 2 MHz Video NF = 3.5 dB	-52 dBm min
Video Impedance (R <sub>v</sub> )	BW = 2 MHz	2.5KΩ min 4.5KΩ max
Voltage Output (E <sub>o</sub> )	BW = 2 MHz	5.0 mV min

\* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.